

2SK1608

Silicon N-Channel Power F-MOS FET

■ Features

- High avalanche energy capacity
- V_{GS} : 30V guaranteed
- Low $R_{DS(on)}$, high-speed switching characteristic

■ Applications

- High-speed switching (switching power supply)
- For high-frequency power amplification

■ Absolute Maximum Ratings ($T_C = 25^\circ\text{C}$)

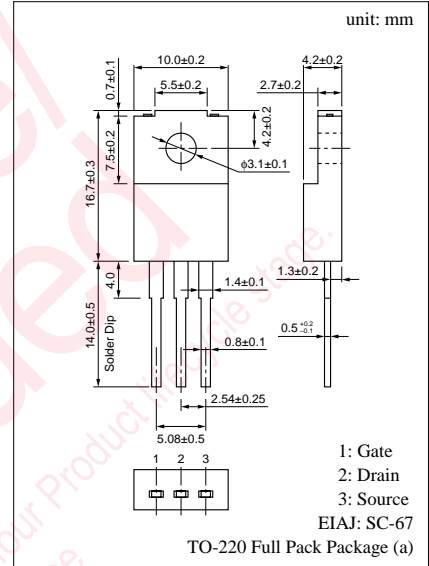
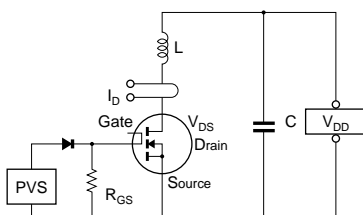
Parameter	Symbol	Rated	Unit	
Drain to Source breakdown voltage	V_{DSS}	500	V	
Gate to Source voltage	V_{GSS}	± 30	V	
Drain current	DC	I_D	± 5	A
	Pulse	I_{DP}	± 10	A
Avalanche energy capacity	EAS*	100	mJ	
Allowable power dissipation	$T_C = 25^\circ\text{C}$	P_D	50	W
	$T_a = 25^\circ\text{C}$		2	
Channel temperature	T_{ch}	150	$^\circ\text{C}$	
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$	

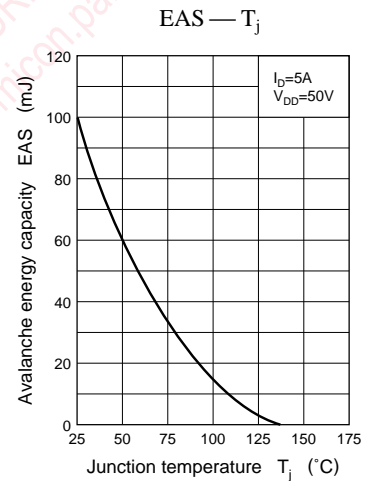
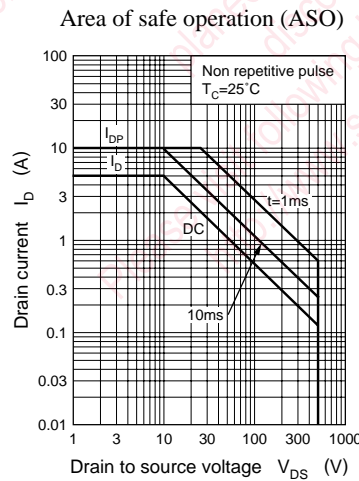
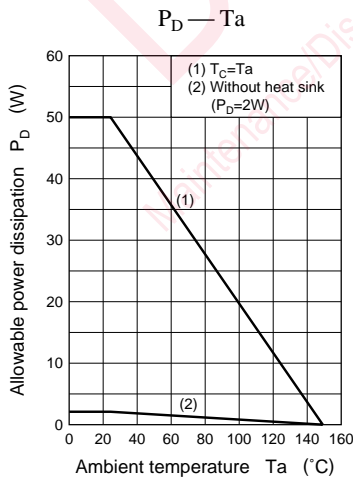
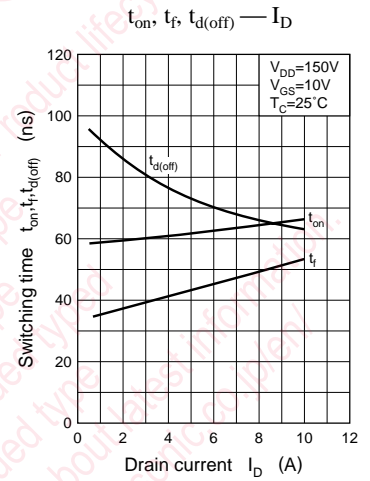
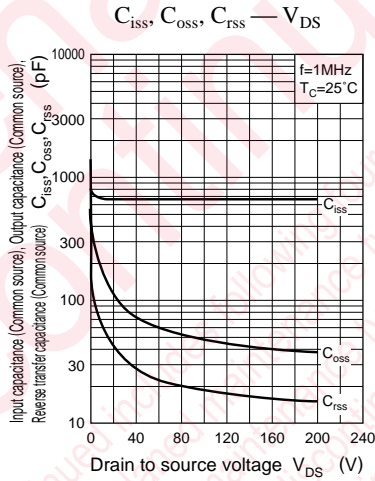
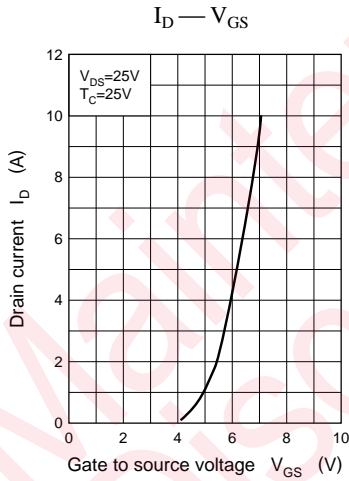
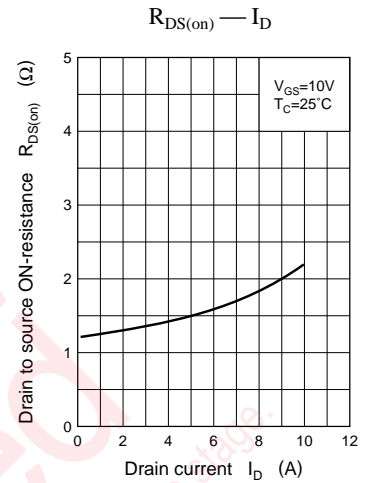
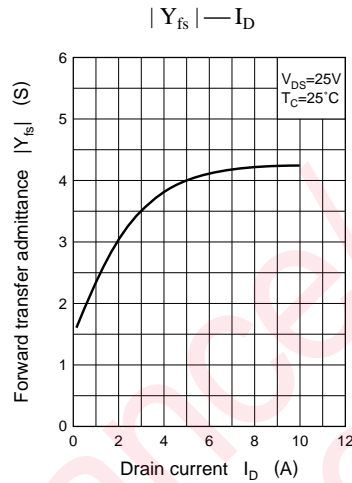
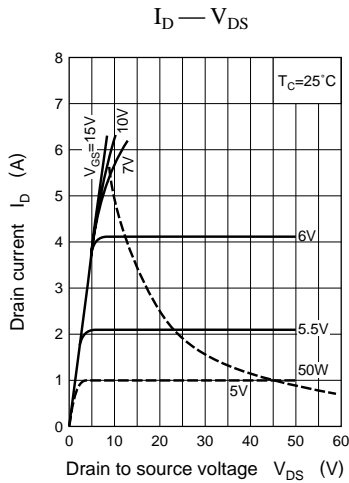
* Single pulse

■ Electrical Characteristics ($T_C = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	min	typ	max	Unit	
Drain to Source cut-off current	I_{DSS}	$V_{DS} = 400\text{V}, V_{GS} = 0$			0.1	mA	
Gate to Source leakage current	I_{GSS}	$V_{GS} = \pm 30\text{V}, V_{DS} = 0$			± 1	μA	
Drain to Source breakdown voltage	V_{DSS}	$I_D = 1\text{mA}, V_{GS} = 0$	500			V	
Avalanche energy capacity	EAS*	$L = 8\text{mH}, I_D = 5\text{A}, V_{DD} = 50\text{V}$	100			mJ	
Gate threshold voltage	V_{th}	$V_{DS} = 25\text{V}, I_D = 1\text{mA}$	1		5	V	
Drain to Source ON-resistance	$R_{DS(on)}$	$V_{GS} = 10\text{V}, I_D = 3\text{A}$		1.35	1.7	Ω	
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = 25\text{V}, I_D = 3\text{A}$	2	3.5		S	
Input capacitance (Common Source)	C_{iss}	$V_{DS} = 20\text{V}, V_{GS} = 0, f = 1\text{MHz}$		700		pF	
Output capacitance (Common Source)	C_{oss}				100		pF
Reverse transfer capacitance (Common Source)	C_{rss}				35		pF
Turn-on time	t_{on}	$V_{GS} = 10\text{V}, I_D = 3\text{A}$ $V_{DD} = 150\text{V}, R_L = 50\Omega$		60		ns	
Fall time	t_f				40		ns
Turn-off time (delay time)	$t_{d(off)}$				80		ns

* Avalanche energy capacity test circuit





Request for your special attention and precautions in using the technical information and semiconductors described in this book

- (1) If any of the products or technical information described in this book is to be exported or provided to non-residents, the laws and regulations of the exporting country, especially, those with regard to security export control, must be observed.
- (2) The technical information described in this book is intended only to show the main characteristics and application circuit examples of the products, and no license is granted under any intellectual property right or other right owned by our company or any other company. Therefore, no responsibility is assumed by our company as to the infringement upon any such right owned by any other company which may arise as a result of the use of technical information described in this book.
- (3) The products described in this book are intended to be used for standard applications or general electronic equipment (such as office equipment, communications equipment, measuring instruments and household appliances).
Consult our sales staff in advance for information on the following applications:
 - Special applications (such as for airplanes, aerospace, automobiles, traffic control equipment, combustion equipment, life support systems and safety devices) in which exceptional quality and reliability are required, or if the failure or malfunction of the products may directly jeopardize life or harm the human body.
 - Any applications other than the standard applications intended.
- (4) The products and product specifications described in this book are subject to change without notice for modification and/or improvement. At the final stage of your design, purchasing, or use of the products, therefore, ask for the most up-to-date Product Standards in advance to make sure that the latest specifications satisfy your requirements.
- (5) When designing your equipment, comply with the range of absolute maximum rating and the guaranteed operating conditions (operating power supply voltage and operating environment etc.). Especially, please be careful not to exceed the range of absolute maximum rating on the transient state, such as power-on, power-off and mode-switching. Otherwise, we will not be liable for any defect which may arise later in your equipment.
 - Even when the products are used within the guaranteed values, take into the consideration of incidence of break down and failure mode, possible to occur to semiconductor products. Measures on the systems such as redundant design, arresting the spread of fire or preventing glitch are recommended in order to prevent physical injury, fire, social damages, for example, by using the products.
- (6) Comply with the instructions for use in order to prevent breakdown and characteristics change due to external factors (ESD, EOS, thermal stress and mechanical stress) at the time of handling, mounting or at customer's process. When using products for which damp-proof packing is required, satisfy the conditions, such as shelf life and the elapsed time since first opening the packages.
- (7) This book may be not reprinted or reproduced whether wholly or partially, without the prior written permission of Matsushita Electric Industrial Co., Ltd.